Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	7404	((257/52) or (257/57) or (257/59) or (257/66) or (257/72) or (257/346) or (257/365)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/24 13:22
L3	7404	((257/52) or (257/57) or (257/59) or (257/66) or (257/72) or (257/346) or (257/365)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/24 13:23
L4	19	3 and pixel and (tft thin adj film adj transistor tft semiconductor adj device field adj effect adj transistor) and base adj film and (LDD (lightly adj doped lightly-doped) adj drain) and (silicon adj oxynitride near2 hydrogenated SiON:H H:SiON SiONH) and (concentration density) near6 (oxygen hydrogen nitrogen "O.sub.2" "H.sub.2" "N.sub.2")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/24 13:27
L5	1	((sakama near2 mitsunori).in. (asami near2 taketomi).in. (ishimaru near2 noriko)".in" (yamazaki near2 shunpei).in. (semiconductor near1 energy).as.) and pixel.clm. and (tft thin adj film adj transistor tft semiconductor adj device field adj effect adj transistor).clm. and base adj film.clm. and (LDD (lightly adj doped lightly-doped) adj drain).clm. and (silicon adj oxynitride near2 hydrogenated SiON:H H:SiON SiONH).clm. and (concentration density) near6 (oxygen hydrogen nitrogen "O.sub.2" "H.sub.2" "N.sub.2").clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/11/24 13:29
S1	3	"669284".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 14:50
S2	377	(257/365).CCLS.	US-PGPUB; USPAT	OR	OFF	2004/12/28 16:33

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S3	18	S2 and oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/28 16:39
S4	1	S2 and oxynitride and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/28 16:40
S5	853	(tft thin adj film adj transistor) and oxynitride and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/28 16:40
S6	81	(tft thin adj film adj transistor) and hydrogenated near4 oxynitride and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/28 16:41
S7	81	(tft thin adj film adj transistor) and hydrogenated near3 oxynitride and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 16:49
S8	81	(tft thin adj film adj transistor) and (gate near3 insulat$3 oxide) and hydrogenated near3 oxynitride and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 16:53
S9	2	(tft thin adj film adj transistor) and (gate near3 insulat$3 oxide) near8 hydrogenated near3 oxynitride and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 16:51
S10	1	(tft thin adj film adj transistor) and (gate near3 (insulat$3 oxide)) near8 hydrogenated near3 oxynitride and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 16:51
S11	2	jp-08055847$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 17:21
S12	0	driver adj (region area section portion) and pixel adj (region area section portion) and (tft thin adj film adj transistor) and oxynitride near6 hydrogenated near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 17:24

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S13	10	driver adj (region area section portion) and pixel adj (region area section portion) and (tft thin adj film adj transistor) and oxynitride near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 17:24
S14	6	driver adj (region area section portion) and pixel adj (region area section portion) and (tft thin adj film adj transistor) and oxynitride near6 gate and hydrogenated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 17:24
S15	4	driver adj (region area section portion) and pixel adj (region area section portion) and (tft thin adj film adj transistor) and oxynitride near6 gate and hydrogenated and (lightly adj doped adj drain ldd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 17:26
S16	4	driver adj (region area section portion) and pixel adj (region area section portion) and (tft thin adj film adj transistor) and (SiON oxynitride) near6 gate and hydrogenated and (lightly adj doped adj drain ldd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 17:29
S17	85	driver adj (region area section portion) and pixel adj (region area section portion) and (tft thin adj film adj transistor) and (lightly adj doped adj drain ldd)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 17:34
S18	1	("6834818").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/28 17:35
S19	2	("6384818").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/28 17:37
S20	2	JP-10104663$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/28 17:37
S21	8	(US-20040007748-$ or US-20040238820-$).did. or (US-6064091-$ or US-6384818-$ or US-6740938-$).did. or (JP-08055847-$).did. or (JP-08055847-$ or JP-10104663-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 11:01

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S22	2	jp-08277486$-$.did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 10:51
S23	2	("6384818").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:10
S24	4	("5970384").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:10
S25	0	S24 and pixel near3 circuit and driver near3 circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:11
S26	0	S24 and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:11
S27	0	S24 and pixel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:11
S28	0	S24 and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:21
S29	130	hydrogenated near4 (oxynitride "SiO:N" "Si:ON")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:22
S30	0	hydrogenated near4 ("SiO:N" "Si:ON")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:22
S31	61	hydrogenated near4 oxynitride and (ldd lightly adj doped adj drain) and (tft thin adj film adj transistor) and pixel and driver and (overlap overlapped overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:24

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S33	56	hydrogenated near4 oxynitride and (ldd lightly adj doped adj drain) and (tft thin adj film adj transistor) and pixel near2 (region area portion) and driver near2 (region area portion) and (overlap overlapped overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:25
S34	55	hydrogenated near4 oxynitride and (ldd lightly adj doped adj drain) and (tft thin adj film adj transistor) and pixel near2 (region area portion) and driver near2 (region area portion) and (overlap overlapped overlapping) near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:25
S35	20	hydrogenated near4 oxynitride and (ldd lightly adj doped adj drain) and (tft thin adj film adj transistor) and pixel near2 (region area portion) and driver near2 (region area portion) and (overlap overlapped overlapping) near6 gate and third near3 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:29
S36	55	hydrogenated near4 oxynitride and (ldd lightly adj doped adj drain) and (tft thin adj film adj transistor) and pixel near2 (region area portion) and driver near2 (region area portion) and (overlap overlapped overlapping) near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:29
S37	35	hydrogenated near4 oxynitride and (ldd lightly adj doped adj drain) and (tft thin adj film adj transistor) and pixel near2 (region area portion) and driver near2 (region area portion) and (overlap overlapped overlapping) near6 gate and (S36 not S35)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:35
S38	438	overlap near3 gate near4 (advantage reduce increase)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:35
S39	55	overlap near3 gate near4 (advantage reduce increase) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:35

S40	9	overlap near3 gate near4 (advantage reduce increase) and (thin adj film adj transistor tft).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:40
S41	3	overlap near3 gate near4 (advantage reduce increase) and (thin adj film adj transistor tft).ti. and pixel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:45
S42	259	overlap near3 gate and (thin adj film adj transistor tft).ti. and pixel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:45
S43	75	overlap near3 gate.ti,ab,clm. and (thin adj film adj transistor tft).ti. and pixel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:45
S44	15	overlap near3 gate.ti,ab,clm. and (thin adj film adj transistor tft).ti. and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:46
S45	1	overlap near3 gate.ti,ab,clm. and (thin adj film adj transistor tft).ti. and pixel and driver and oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 11:46
S46	2	("5804878").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 13:44
S49	0	("hydrogenatednear3oxynitridenear 10gateinsulat$3andthinadjfilmadjtra nsistor.ti,ab,clm.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 15:45
S50	0	hydrogenated near3 oxynitride near10 gate adj insulat$3 and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 15:46
S51	1	hydrogenated near3 oxynitride near10 gate adj insulat$3 and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 15:47

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S52	2	SiON near3 hydrogenated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 15:49
S53	25	SiON near3 hydrogenated SiON:H	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 15:51
S54	0	(SiON near3 hydrogenated SiON:H) near20 gate adj (insulation insulating) and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 15:50
S55	0	(SiON near3 hydrogenated SiON:H) near20 gate and thin adj film adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 15:50
S56	0	SiON:H near10 gate adj (insulating insulation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:07
S57	1930	video and personal adj computer and video adj camera and projector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:08
S58	475	video and personal adj computer and video adj camera and projector and (thin adj film adj transistor).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:08
S59	391	video and personal adj computer and video adj camera and projector and (thin adj film adj transistor).ti, ab,clm. and gate adj (insulation insulating) adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:08
S60	187	(video and personal adj computer and video adj camera and projector).ti,ab,clm. and (thin adj film adj transistor).ti,ab,clm. and gate adj (insulation insulating) adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:09

EAST Search History

S61	147	(video and personal adj computer and video adj camera and projector).ti,ab,clm. and (thin adj film adj transistor).ti,ab,clm. and gate adj (insulation insulating) adj film and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:09
S62	0	(video and personal adj computer and video adj camera and projector).ti,ab,clm. and (thin adj film adj transistor).ti,ab,clm. and gate adj (insulation insulating) adj film and pixel adj portion and driver adj portion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:09
S63	0	(video and personal adj computer and video adj camera and projector).ti,ab,clm. and (thin adj film adj transistor).ti,ab,clm. and gate adj (insulation insulating) adj film and pixel and driver adj portion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:10
S64	147	(video and personal adj computer and video adj camera and projector).ti,ab,clm. and (thin adj film adj transistor).ti,ab,clm. and gate adj (insulation insulating) adj film and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:10
S65	78	(video and personal adj computer and video adj camera and projector).ti,ab,clm. and (thin adj film adj transistor).ti,ab,clm. and gate adj (insulation insulating) adj film.ti,ab,clm. and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:12
S66	153	(video and personal adj computer and video adj camera and projector).ti,ab,clm. and (thin adj film adj transistor).ti,ab,clm. and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/29 17:12
S67	12	(US-20040007748-$ or US-20040238820-$).did. or (US-6064091-$ or US-6384818-$ or US-6740938-$ or US-5970384-$ or US-6673659-$ or US-5804878-$). did. or (JP-08055847-$).did. or (JP-08055847-$ or JP-10104663-$ or US-20040169183-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 17:15
S68	211	driver and pixel and tft and video and portable and digital and disk and game and projector	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 17:18

EAST Search History

S69	3576	driver and pixel and tft and video	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 17:18
S70	738	driver and pixel and tft and video and portable and game	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 17:20
S71	2	jp-10101974$-$.did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 17:20
S72	1	jp-11101974$-$.did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 17:31
S73	1177	(electrolumiscence EL) adj (display device) and thin adj film adj transistor.ti,ab,clm.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 17:32
S74	438	(electrolumiscence EL) adj (display device) and thin adj film adj transistor.ti,ab,clm. and pixel and driver	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/29 17:33
S75	2	(electrolumiscence EL) adj (display device) and thin adj film adj transistor.ti,ab,clm. and pixel and driver	JPO	OR	OFF	2004/12/29 17:34
S76	1425	(EL adj display electroluminescence adj display) and (thin adj film adj transistor tft) and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 07:18
S77	292	(EL adj display electroluminescence adj display).ti,ab,clm. and (thin adj film adj transistor tft).ti,ab,clm. and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 07:18
S78	139	(EL adj display electroluminescence adj display).ti,ab,clm. and (thin adj film adj transistor tft).ti,ab,clm. and pixel near3 tft and driver near3 tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 07:23
S79	0	("669284.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 07:22

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S80	3	"669284".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 07:22
S81	292	(EL adj display electroluminescence adj display).ti,ab,clm. and (thin adj film adj transistor tft).ti,ab,clm. and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 07:23
S82	153	((EL adj display electroluminescence adj display).ti,ab,clm. and (thin adj film adj transistor tft).ti,ab,clm. and pixel and driver) not S78	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 09:02
S83	1	"5804878".pn. and source and channel and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 09:40
S84	123	organic adj resin near8 interlayer adj (dielectric insulat$3) adj (film layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 09:41
S85	75	organic adj resin near8 interlayer adj (dielectric insulat$3) adj (film layer) and (thin adj film adj transistor tft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 09:42
S86	9	organic adj resin near8 interlayer adj (dielectric insulat$3) adj (film layer).ti,ab,clm. and (thin adj film adj transistor tft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 09:44
S87	7	organic adj resin near8 interlayer adj (dielectric insulat$3) adj (film layer).ti,ab,clm. and (thin adj film adj transistor tft).ti,ab,clm. and pixel adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 09:45
S88	2	"5784073".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 09:47
S89	1	"5784073".pn. and organic adj resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 10:28

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S90	1	"5784073".pn. and organic adj resin and flatten$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 11:09
S91	2068	((257/365) or (257/346) or (257/365) or (257/72)).CCLS.	US-PGPUB; USPAT	OR	OFF	2004/12/30 11:29
S92	513	S91 and gate and pixel and driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 13:43
S93	11	(("5,323,042") or ("5,970,384") or ("6,166,414") or ("6,198,133") or ("6,281,552") or ("6,306,694") or ("6,399,988") or ("6,429,483") or ("6,524,895") or ("6,531,713") or ("6,534,826")).PN.	USPAT	OR	OFF	2004/12/30 13:44
S94	9	(("5,247,190") or ("5,399,507") or ("5,504,020") or ("5,640,067") or ("5,643,826") or ("5,897,328") or ("5,923,962") or ("5,970,384") or ("6,461,899")).PN.	USPAT	OR	OFF	2004/12/30 13:48
S95	9	(US-6461899-$ or US-5970384-$ or US-5923962-$ or US-5897328-$ or US-5643826-$ or US-5640067-$ or US-5504020-$ or US-5399507-$ or US-5247190-$).did.	USPAT	OR	OFF	2004/12/30 13:49
S96	2	jp-04369271$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 13:52
S97	2	jp-05102483$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 13:53
S98	2	jp-07335900$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 13:54
S99	2	jp-08078329$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 13:55

S10 0	2	jp-10135468$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 13:55
S10 1	2	jp-10135469$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:11
S10 2	0	w0-9013148$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:11
S10 3	0	w0-90013148$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:11
S10 4	0	w0-1990013148$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:11
S10 5	0	wo-1990013148$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:11
S10 6	0	wo-90013148$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:11
S10 7	1	wo-9013148$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:13
S10 8	1	jp-07130652$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:14
S10 9	2	jp-08055846$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:21

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S11 0	2	jp-08055847$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:22
S11 1	2	jp-08055848$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:23
S11 2	2	jp-10092576$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:25
S11 3	2	jp-10247735$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/30 14:25
S11 4	57	(US-20040007748-$ or US-20040238820-$).did. or (US-5804878-$ or US-5970384-$ or US-6064091-$ or US-6384818-$ or US-6673659-$ or US-6740938-$ or US-5684365-$ or US-5784073-$ or US-6777763-$ or US-6747289-$ or US-6448612-$ or US-6441399-$ or US-6259120-$ or US-6160269-$ or US-5818070-$ or US-5789762-$ or US-5712495-$ or US-5677549-$ or US-5619045-$ or US-5572046-$ or US-6534826-$ or US-6531713-$ or US-6524895-$ or US-6429483-$ or US-6399988-$ or US-6306694-$). did. or (US-6281552-$ or US-6198133-$ or US-6166414-$ or US-5323042-$ or US-6461899-$ or US-5923962-$ or US-5897328-$ or US-5643826-$ or US-5640067-$ or US-5504020-$ or US-5399507-$ or US-5247190-$).did. or (JP-08055847-$ or JP-04369271-$ or JP-05102483-$ or JP-07335900-$ or JP-08078329-$ or JP-10135468-$ or JP-10135469-$ or JP-08055846-$ or JP-08055848-$ or JP-10092576-$ or JP-10247735-$).did. or (JP-08055847-$ or JP-10104663-$ or JP-11101974-$ or US-20040169183-$ or EP-423283-$ or EP-651431-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/30 15:02

S11 5	57	(US-20040007748-$ or US-20040238820-$).did. or (US-5804878-$ or US-5970384-$ or US-6064091-$ or US-6384818-$ or US-6673659-$ or US-6740938-$ or US-5684365-$ or US-5784073-$ or US-6777763-$ or US-6747289-$ or US-6448612-$ or US-6441399-$ or US-6259120-$ or US-6160269-$ or US-5818070-$ or US-5789762-$ or US-5712495-$ or US-5677549-$ or US-5619045-$ or US-5572046-$ or US-6534826-$ or US-6531713-$ or US-6524895-$ or US-6429483-$ or US-6399988-$ or US-6306694-$). did. or (US-6281552-$ or US-6198133-$ or US-6166414-$ or US-5323042-$ or US-6461899-$ or US-5923962-$ or US-5897328-$ or US-5643826-$ or US-5640067-$ or US-5504020-$ or US-5399507-$ or US-5247190-$).did. or (JP-08055847-$ or JP-04369271-$ or JP-05102483-$ or JP-07335900-$ or JP-08078329-$ or JP-10135468-$ or JP-10135469-$ or JP-08055846-$ or JP-08055848-$ or JP-10092576-$ or JP-10247735-$).did. or (JP-08055847-$ or JP-10104663-$ or JP-11101974-$ or US-20040169183-$ or EP-423283-$ or EP-651431-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2004/12/30 15:02
S11 6	25	"5970384"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 06:19
S11 7	4	("5970384").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/20 06:19
S11 8	0	("669284.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 14:50
S11 9	3	"669284".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 15:10

S12 0	4	("5970384").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 16:25
S12 1	0	("teos(").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 16:25
S12 2	0	("teos.ti.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 16:26
S12 3	0	"teos ("	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 16:26
S12 4	2899	teos.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 16:26
S12 5	288	teos.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 16:26
S12 6	288	teos.ti. and "(teos)"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 17:20
S12 7	2	("5804878").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 19:22
S12 8	0	("baseadjfilmnear6oxynitride").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 19:22
S12 9	237	base adj film near6 oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 19:22

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S13 0	10	base adj film near6 oxynitride near6 hydrogenated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 19:27
S13 1	11	base adj (layer film) near15 oxynitride near15 hydrogenat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 19:28
S13 2	13	base adj (layer film) near15 oxynitride near15 hydrogen$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 19:41
S13 3	5480	((257/52) or (257/57) or (257/59) or (257/66) or (257/72) or (257/346) or (257/365)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/18 19:42
S13 4	110	S133 and oxynitride and (hydrogen hydrogenat$3) and nitrogen near10 (density concentration abundance) and (buffer base) and (field adj effect adj transistor tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 19:45
S13 5	187747	S133 and oxynitride and (hydrogen hydrogenat$3) and nitrogen near10 (density concentration abundance) near10 (base buffer) (field adj effect adj transistor tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/18 19:46
S13 6	1	S133 and oxynitride and (hydrogen hydrogenat$3) and nitrogen near10 (density concentration abundance) near10 (base buffer) and (field adj effect adj transistor tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB·	OR	ON	2005/06/18 19:46
S13 7	3	"669284".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/17 11:13
S13 8	255	"5,323,042" "5,970,384" "6,166,414" "6,198,133" "6,281,552" "6,306,694" "6,399,988" "6,429,483" "6,524,895" "6,531,713" "6,534,826"	US-PGPUB; USPAT	OR	OFF	2005/11/12 11:10

S13 9	11	(("5,323,042") or ("5,970,384") or ("6,166,414") or ("6,198,133") or ("6,281,552") or ("6,306,694") or ("6,399,988") or ("6,429,483") or ("6,524,895") or ("6,531,713") or ("6,534,826")).PN.	US-PGPUB; USPAT	OR	OFF	2005/11/12 11:11
S14 0	2	jp-08055847$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 11:12
S14 1	2	jp-08055846$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 11:12
S14 2	2	jp-08055848$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 11:12
S14 3	2	("5594569").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 11:19
S14 4	11	(("3,765,935") or ("5,274,602") or ("5,972,437") or ("6,174,816") or ("20010011725") or ("6,285,042") or ("6,291,363") or ("6,323,528") or ("6,335,541") or ("6,348,420") or ("6,573,195")).PN.	US-PGPUB; USPAT	OR	OFF	2005/11/12 11:21
S14 5	13	S143 S144	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 11:21
S14 6	3	"669284".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 11:22
S14 7	1	(US-20040238820-$).did.	US-PGPUB	OR	OFF	2005/11/12 13:17
S14 8	0	S147 and terada	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 11:38

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S14 9	4	("5970384").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 13:18
S15 0	2	("5804878").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 13:42
S15 1	145	hydrogenated adj silicon adj oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 13:43
S15 2	154	hydrogenat$3 near2 silicon adj oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 13:43
S15 3	35	hydrogenat$3 near2 silicon adj oxynitride and hydrogen adj (concentration content)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 13:44
S15 4	3	hydrogenat$3 near2 silicon adj oxynitride same hydrogen adj (concentration content)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 13:47
S15 5	11	hydrogenat$3 near2 silicon adj oxynitride and ((H hydrogen) adj (concentration content)) same ((O oxygen) adj (concentration density))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 13:55
S15 6	12	hydrogenat$3 near2 silicon adj oxynitride and substrate near1 temperature and (electric adj2 discharge) near2 power near2 density	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 13:56
S15 7	12	hydrogenat$3 near2 silicon adj oxynitride and substrate near1 temperature and (electric adj2 discharge) near2 power near2 density and gate adj insulat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 14:00
S15 8	87	hydrogenat$3 near2 silicon adj oxynitride and substrate near1 temperature and electric near2 power near2 density and gate adj insulat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 14:00

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S15 9	87	hydrogenat$3 near2 silicon adj oxynitride and (substrate near1 temperature) same ((electric near2 power) near2 density) and gate adj insulat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 14:11
S16 0	2	jp-08055847$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 14:06
S16 1	0	hydrogenat$3 near2 silicon adj oxynitride and (substrate near1 temperature) same ((electric near2 power) near2 density) and gate adj insulat$3 and @ad<"19990531"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 14:12
S16 2	0	hydrogenat$3 near2 silicon adj oxynitride and (substrate near1 temperature) same ((electric near2 power) near2 density) and gate adj insulat$3 and @ad<"20000531"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 14:13
S16 3	20	hydrogenat$3 near2 silicon adj oxynitride and (substrate near1 temperature) same ((electric near2 power) near2 density) and gate adj insulat$3 and @ad<"20010531"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 14:13
S16 4	1	(US-20040238820-$).did.	US-PGPUB	OR	OFF	2005/11/12 15:33
S16 5	1	S164 and base	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 16:05
S16 6	0	"Si-H" near6 "Si-OH" near6 (nitridization nitridizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 16:06
S16 7	3	"Si-H" near6 "Si-OH" and (nitridization nitridizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 16:06
S16 8	3	"Si-H" near6 "Si-OH" and (nitridization nitridizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:11

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S16 9	6	"Si-H" near5 (bond adj strength)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:12
S17 0	0	"Si-OH" near5 (bond adj strength)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:31
S17 1	1	"O-H" near5 (bond adj strength)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:32
S17 2	10	("OH" "O-H") near5 (bond adj strength)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:32
S17 3	0	("OH" "O-H") near5 (bond adj strength) near4 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:33
S17 4	0	("OH" "O-H") near5 (bond adj strength) near10 (silicon "SiO:H")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:35
S17 5	0	("OH" "O-H") near5 (dissociation adj energy bond adj strength) near10 (silicon "SiO:H")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:35
S17 6	0	("OH" "O-H" "H-O" HO) near5 (dissociation adj energy bond adj strength) near10 (silicon "SiO:H")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:35
S17 7	27	("OH" "O-H" "H-O" HO) near5 (dissociation adj energy bond adj strength)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 16:59
S17 8	24	(Si-O) near5 (dissociation adj energy bond adj strength)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 17:08

S17 9	20	Si-N near6 (bond adj strength dissociation adj energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 17:09
S18 0	20	"Si-N" near6 (bond adj strength dissociation adj energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 17:13
S18 1	11	("O-N" "N-O") near6 (bond adj strength dissociation adj energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 17:25
S18 2	208	SiON near4 structure and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 17:32
S18 3	167	hydrogenat$3 near1 (silicon adj oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 17:33
S18 4	70	hydrogenat$3 near1 (silicon adj oxynitride) and atomic near3 "%"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 17:37
S18 5	3	hydrogenat$3 near1 (silicon adj oxynitride) and atomic near3 "%" and @ad<"19990603"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 18:26
S18 6	5762	((257/52) or (257/57) or (257/59) or (257/66) or (257/72) or (257/346) or (257/365)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/12 18:27
S18 7	1	(silicon adj oxynitride near3 hydrogenat$3 "SiON:H").ti,ab,clm. and (density concentration abundance) near3 (oxygen hydrogen nitrogen O H N).ti,ab,clm. and gate.ti,ab,clm. and base adj (layer film).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/12 18:30

S18 8	168	hydrogenated near2 silicon adj oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/09 14:34
S18 9	150	hydrogenated near2 silicon adj oxynitride and concentration	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:35
S19 0	2	hydrogenated near2 silicon adj oxynitride and concentration and SOI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:36
S19 1	27	hydrogenated near2 silicon adj oxynitride and concentration near4 (hydrogen H)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:36
S19 2	27	hydrogenated near2 (silicon adj oxynitride SiON SiO:N SiN:O) and concentration near4 (hydrogen H)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:37
S19 3	27	hydrogenated near2 (silicon adj oxynitride SiON "SiO:N" "SiN:O") and concentration near4 (hydrogen H)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:43
S19 4	30	("SiON:H" "SiN:OH" SIONH SIOHN (hydrogenated near2 (silicon adj oxynitride SiON "SiO:N" "SiN:O"))) and concentration near4 (hydrogen H)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:48
S19 5	10	("SiON:H" "SiN:OH" SIONH SIOHN (hydrogenated near2 (silicon adj oxynitride SiON "SiO:N" "SiN:O"))) and concentration near4 (hydrogen H) not (semiconductor near1 energy.as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:51
S19 6	8	(("SiON:H" "SiN:OH" SIONH SIOHN (hydrogenated near2 (silicon adj oxynitride SiON "SiO:N" "SiN:O"))) and concentration near4 (hydrogen H) and gate) not (semiconductor near1 energy.as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:53

S19 7	3	(("SiON:H" "SiN:OH" SIONH SIOHN (hydrogenated near2 (silicon adj oxynitride SiON "SiO:N" "SiN:O")) near10 (concentration near4 (hydrogen H))) and concentration near4 (hydrogen H) and gate) not (semiconductor near1 energy.as.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/09 14:54
S19 8	1	(US-20040238820-$).did.	US-PGPUB	OR	OFF	2006/07/11 16:20
S19 9	0	S198 and gate with base with oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/11 16:20
S20 0	0	S198 and gate with oxygen and base with oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 16:25
S20 1	1	S198 and gate with oxygen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/11 16:39
S20 2	3286	((257/299) or (257/901) or (327/534) or (327/535) or (327/536) or (327/537)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/22 17:02
S20 3	6	(("5804878") or ("5970384")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 11:06
S20 4	1577	(insulati$2 adj surface base) near4 hydrogenated	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:07
S20 5	14	(insulati$2 adj surface base) near4 (hydrogenated adj silicon adj oxynitride "SiON:H" "H:SiON")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:17
S20 6	0	(insulati$2 adj surface base) near4 (hydrogenated adj silicon adj oxynitride "SiON:H" "H:SiON") and @ad<"20000601"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:10

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S20 9	0	(hydrogenated adj silicon adj oxynitride "SiON:H" "H:SiON" "HSiON" "SiONH" "SiNOH" "SiN-OH") and ("SOI" TFT OTFT) and @ad<"2000601"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:19
S21 0	2	(hydrogenated adj silicon adj oxynitride "SiON:H" "H:SiON" "HSiON" "SiONH" "SiNOH" "SiN-OH") and ("SOI" TFT OTFT) and @ad<"20000601"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 11:25
S21 1	12	(hydrogenated adj silicon adj oxynitride "SiON:H" "H:SiON" "HSiON" "SiONH" "SiNOH" "SiN-OH") and ("SOI" TFT OTFT) and kimura. in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:24
S21 2	6	(("5804878") or ("5970384")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:25
S21 3	5	S212 and (hydrogenated hydrogen channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:25
S21 4	14	(insulati$2 adj surface base) near4 (hydrogenated adj silicon adj oxynitride "SiON:H" "H:SiON" "HSiON" "SiONH" "SiNOH" "SiN-OH")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:32
S21 5	10	(("6077731") or ("7056381")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:34
S21 6	2	S215 and hydrogenat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:35
S21 7	1	S215 and hydrogenat$3 and "485"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:39
S21 8	5	"181788".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:43

S21 9	0	jp-2000058856$-$.did	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:43
S22 0	0	jp-200058856$-$.did	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:44
S22 1	0	jp-2000058856$-$.did	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:44
S22 2	3	"2000058856"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/29 14:44
S22 3	156	(hydrogenated adj silicon adj oxynitride "SiON:H" "H:SiON" "HSiON" "SiONH" "SiNOH" "SiN-OH") and ("SOI" TFT OTFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:48
S22 4	222	(hydrogenated adj silicon adj ((oxide near1 nitride) oxynitride) "SiON:H" "H:SiON" "HSiON" "SiONH" "SiNOH" "SiN-OH") and ("SOI" TFT OTFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 14:50
S22 5	2	(hydrogenated adj silicon adj ((oxide near1 nitride) oxynitride) "SiON:H" "H:SiON" "HSiON" "SiONH" "SiNOH" "SiN-OH") and ("SOI" TFT OTFT) and @ad<"20000601"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:00
S22 6	0	S212 and (hydrogenated adj silicon adj ((oxide near1 nitride) oxynitride) "SiON:H" "H:SiON" "HSiON" "SiONH" "SiNOH" "SiN-OH") and @ad<"20000601"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:03
S22 7	2	S212 and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:10
S22 8	0	S212 and channel and (LDD lightly adj doped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:12

S22 9	2	S212 and channel and (LDD lightly adj doped drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:16
S23 0	4	"669282".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/29 15:16
S23 1	41	"5804878"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 18:24
S23 2	2	("5804878").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 18:24
S23 3	4	("5970384").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 18:41
S23 4	2	jp-06318703$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 18:43
S23 5	2	"5773325".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/19 18:43
S23 6	153	("SiON:H" hydrogenated adj silicon adj oxynitride) and gate adj insulati$2 adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:33
S23 7	0	("SiON:H" hydrogenated adj silicon adj oxynitride) and gate adj insulati$2 adj film and atomic adj weight	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:33
S23 8	88	("SiON:H" hydrogenated adj silicon adj oxynitride) and gate adj insulati$2 adj film and "%"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:33

EAST Search History

S23 9	0	("SiON:H" hydrogenated adj silicon adj oxynitride) near6 "%" and gate adj insulati$2 adj film and "%"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:34
S24 0	1	("SiON:H" hydrogenated adj silicon adj oxynitride) near20 "%" and gate adj insulati$2 adj film and "%"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:36
S24 1	1	("SiON:H" hydrogenated adj silicon adj oxynitride) near20 "%" and insulati$2 adj film and "%"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:36
S24 2	3	("SiON:H" hydrogenated adj silicon adj oxynitride) near20 "%"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:39
S24 3	3	("SiON:H" hydrogenated adj silicon adj oxynitride) near20 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:40
S24 4	3	("SiON:H" hydrogenated adj silicon adj oxynitride) near20 "%"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:42
S24 5	118	("SiON:H" hydrogenated adj silicon adj oxynitride) and "257"/$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 09:43
S24 6	8	(("SiON:H" hydrogenated adj silicon adj oxynitride) and "257"/$7.ccls.) and defect near20 (bonding bond)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 10:05
S24 7	211	("SiON:H" hydrogenated adj silicon adj oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 12:29
S24 8	41	(("SiON:H" hydrogenated adj silicon adj oxynitride) ((pcvd lvcd) near3 oxynitride)) near10 (interlayer adj insulati$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 12:31

S249	1	(US-20040238820-$).did.	US-PGPUB	OR	OFF	2006/12/20 12:43
S250	24332	(US-20040238820-$)".did.and" interlayer	US-PGPUB	OR	OFF	2006/12/20 12:43
S251	1	S249 and interlayer	US-PGPUB	OR	OFF	2006/12/20 12:44
S252	0	"5804878".pn. and interlayer	US-PGPUB	OR	OFF	2006/12/20 12:44
S253	2	("5804878").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/20 12:45
S254	1	S253 and interlayer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/20 12:45
S255	4	("5970384").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/20 12:46
S256	1	S255 and interlayer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/20 12:46
S257	2	jp-06318703$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/20 15:33
S258	2	"5773325".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/20 15:54
S259	5575	((257/52) or (257/57) or (257/59) or (257/60) or (257/72) or (257/346) or (257/365)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/20 15:54

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S26 0	16	S259 and silicon adj oxynitride with (hydrogen hydrogenated) and gate adj electrode and overlap$4 and pixel and (concentration density abundance) near10 (hydrogen H) and (concentration density abundance) near10 (nitrogen N) and (concentration density abundance) near10 (oxygen O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/20 15:57
S26 1	16	S259 and silicon adj oxynitride with (hydrogen hydrogenated) and gate adj electrode and overlap$4 and pixel and (concentration density abundance) near10 (hydrogen H) and (concentration density abundance) near10 (nitrogen N) and (concentration density abundance) near10 (oxygen O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 15:58
S26 2	1	S259 and silicon adj oxynitride with (hydrogen hydrogenated).clm. and gate adj electrode.clm. and overlap$4.clm. and pixel.clm. and (concentration density abundance) near10 (hydrogen H).clm. and (concentration density abundance) near10 (nitrogen N).clm. and (concentration density abundance) near10 (oxygen O).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/20 15:59
S26 3	4	("5970384").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/11/24 13:21